

## POWER SCHOTTKY RECTIFIER

### MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	2 x 120 A
$V_{RRM}$	45 V
$V_F$ (max)	0.67 V

### FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- EXTREMELY FAST SWITCHING
- LOW THERMAL RESISTANCE
- INSULATED PACKAGE:  
Insulating voltage = 2500 V<sub>(RMS)</sub>  
Capacitance = 45pF
- AVALANCHE CAPABILITY SPECIFIED

### DESCRIPTION

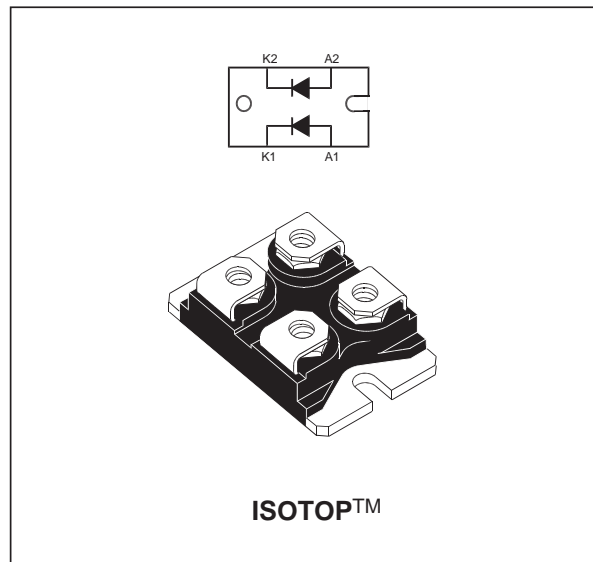
Dual power Schottky rectifier suited for Switched Mode Power Supplies and high frequency DC to DC converters.

Packaged in ISOTOP, this device is especially intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.

### ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter		Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage		45	V
$I_{F(RMS)}$	RMS forward current		170	A
$I_{F(AV)}$	Average forward current	$T_c = 80^\circ\text{C}$ $\delta = 0.5$	Per diode 240	A
$I_{FSM}$	Surge non repetitive forward current	$t_p = 10$ ms Sinusoidal	1500	A
$I_{RRM}$	Repetitive peak reverse current	$t_p = 2$ $\mu\text{s}$ $F = 1$ kHz square	2	A
$I_{RSM}$	Non repetitive peak reverse current	$t_p = 100$ $\mu\text{s}$ square	10	A
$P_{ARM}$	Repetitive peak avalanche power	$t_p = 1$ $\mu\text{s}$ $T_j = 25^\circ\text{C}$	43000	W
$T_{stg}$	Storage temperature range		- 55 to + 150	$^\circ\text{C}$
$T_j$	Maximum operating junction temperature		150	$^\circ\text{C}$
$dV/dt$	Critical rate of rise of reverse voltage		10000	V/ $\mu\text{s}$

\* :  $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j-a)}$  thermal runaway condition for a diode on its own heatsink



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THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
R <sub>th(j-c)</sub>	Junction to case	Per diode	0.65	°C/W
		Total	0.28	
R <sub>th(c)</sub>		Coupling	0.10	

When the diodes 1 and 2 are used simultaneously :  
 $\Delta T_j(\text{diode } 1) = P(\text{diode } 1) \times R_{th(j-c)} + P(\text{diode } 2) \times R_{th(c)}$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I <sub>R</sub> *	Reverse leakage current	T <sub>j</sub> = 25°C	V <sub>R</sub> = V <sub>RRM</sub>			2	mA
		T <sub>j</sub> = 125°C				300	
V <sub>F</sub> *	Forward voltage drop	T <sub>j</sub> = 25°C	I <sub>F</sub> = 240 A			0.91	V
		T <sub>j</sub> = 125°C	I <sub>F</sub> = 240 A		0.72	0.87	
		T <sub>j</sub> = 125°C	I <sub>F</sub> = 120 A		0.52	0.67	

Pulse test : \* tp = 5 ms, δ < 2%  
 \*\* tp = 380 μs, δ < 2%

To evaluate the conduction losses use the following equation :  
 $P = 0.47 \times I_{F(AV)} + 0.00167 \times I_{F(RMS)}^2$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

Fig. 2: Average forward current versus ambient temperature (δ= 0.5, per diode).

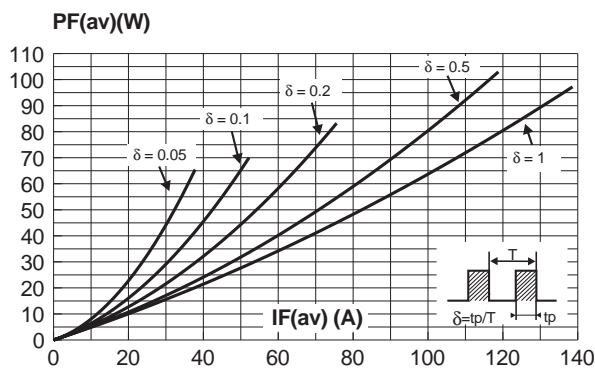


Fig. 3: Normalized avalanche power derating versus pulse duration.

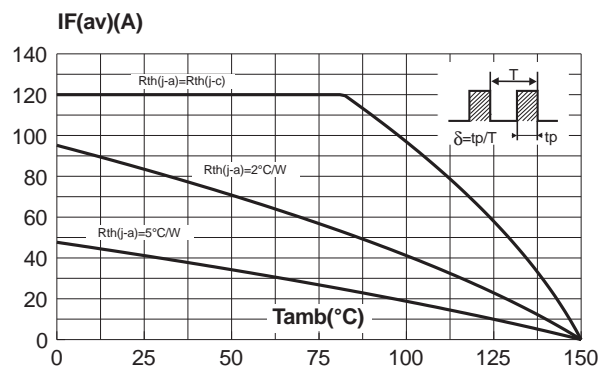
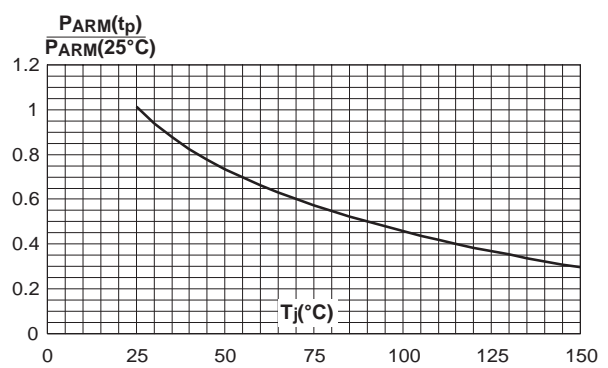
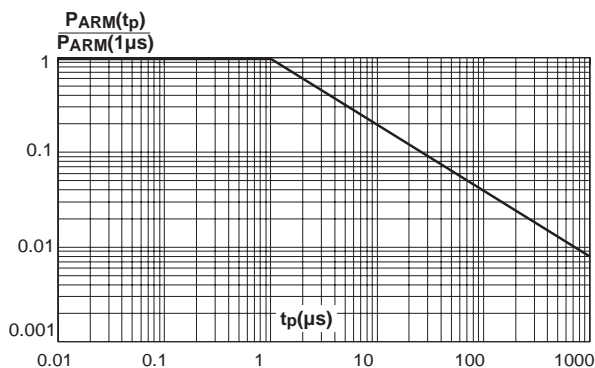
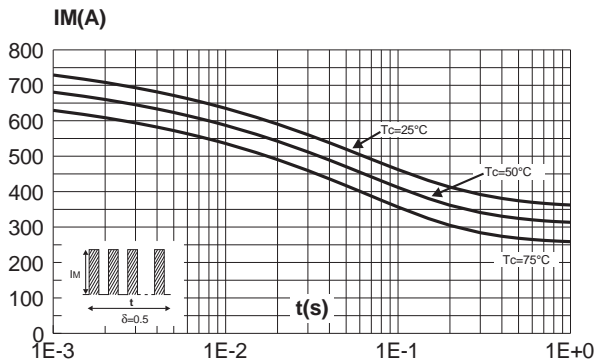


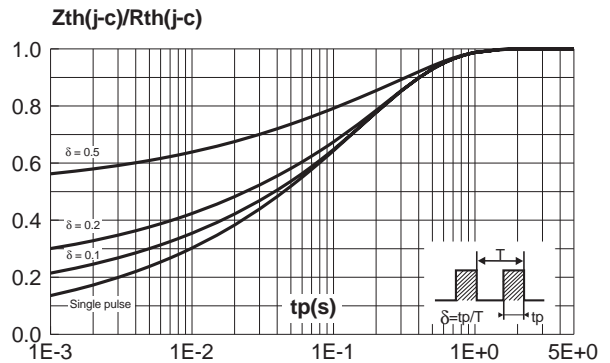
Fig. 4: Normalized avalanche power derating versus junction temperature.



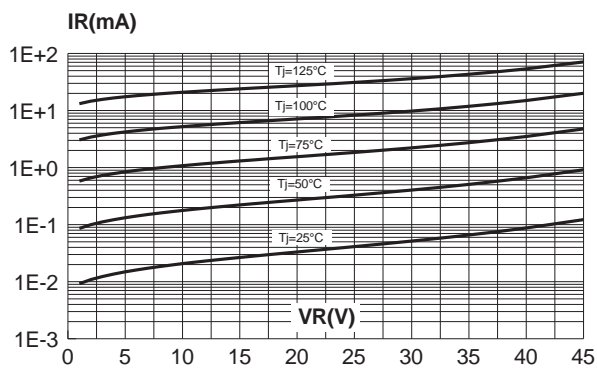
**Fig. 5:** Non repetitive surge peak forward current versus overload duration (maximum values, per diode).



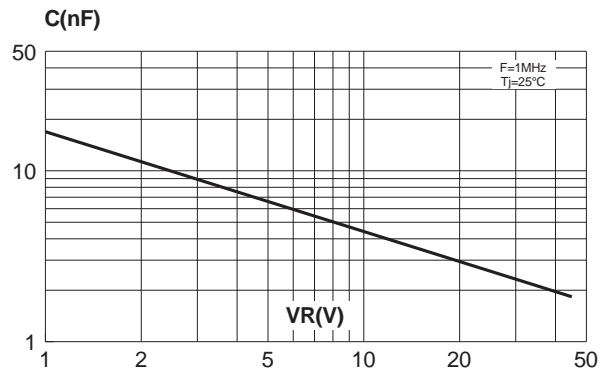
**Fig. 6:** Relative variation of thermal impedance junction to case versus pulse duration (per diode).



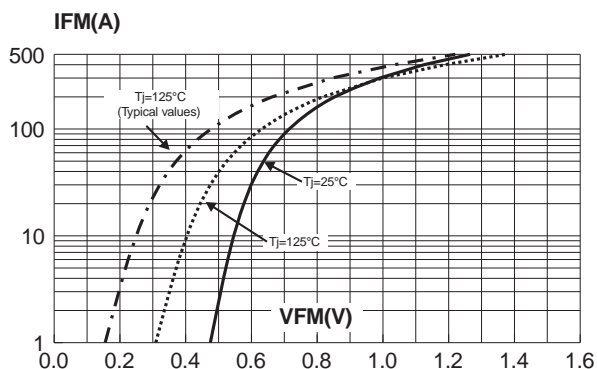
**Fig. 7:** Reverse leakage current versus reverse voltage applied (typical values, per diode).



**Fig. 8:** Junction capacitance versus reverse voltage applied (typical values, per diode).

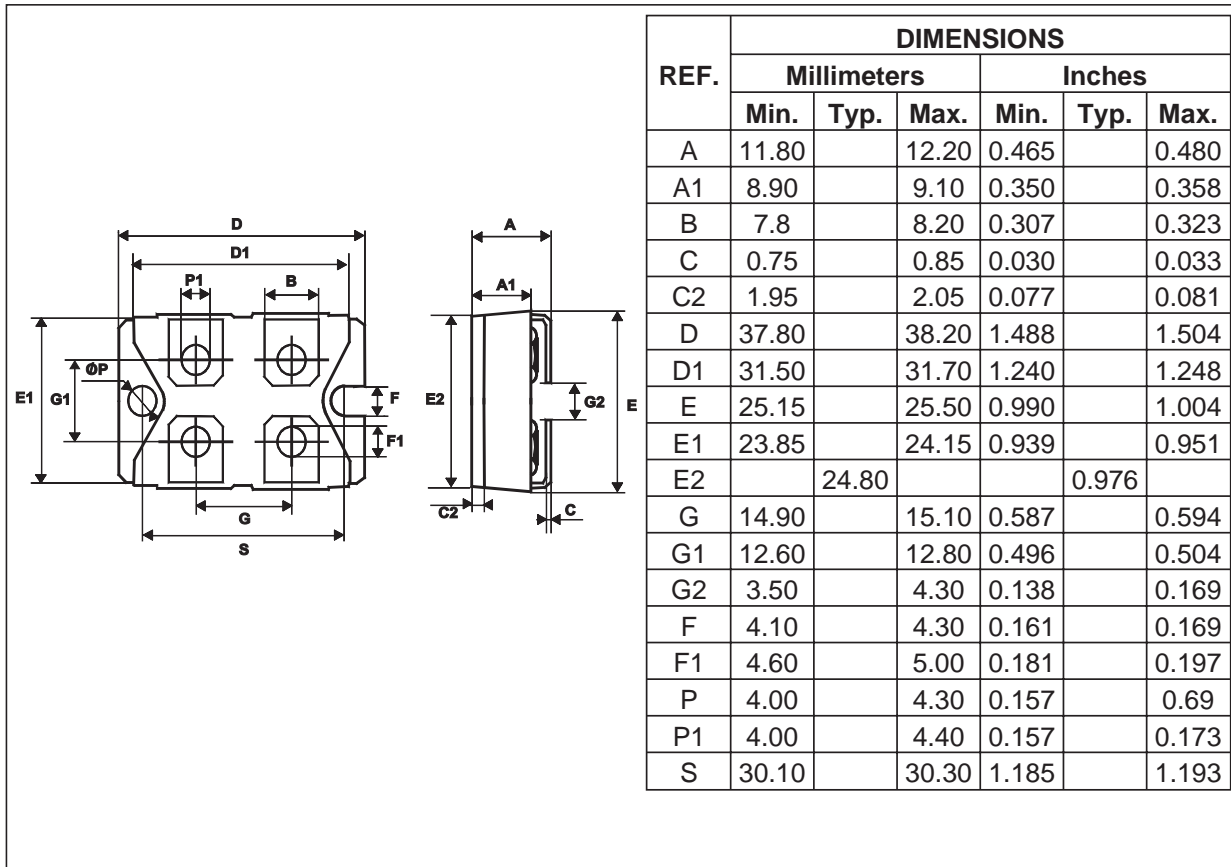


**Fig. 9:** Forward voltage drop versus forward current (maximum values, per diode).



# STPS24045TV

## PACKAGE MECHANICAL DATA ISOTOP



Type	Marking	Package	Weight	Base qty	Delivery mode
STPS24045TV	STPS24045TV	ISOTOP	28 g. (without screws)	10	Tube

- Cooling method: by conduction (C)
- Recommended torque value: 1.3 N.m
- Maximum torque value: 1.5 N.m

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